

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC2710

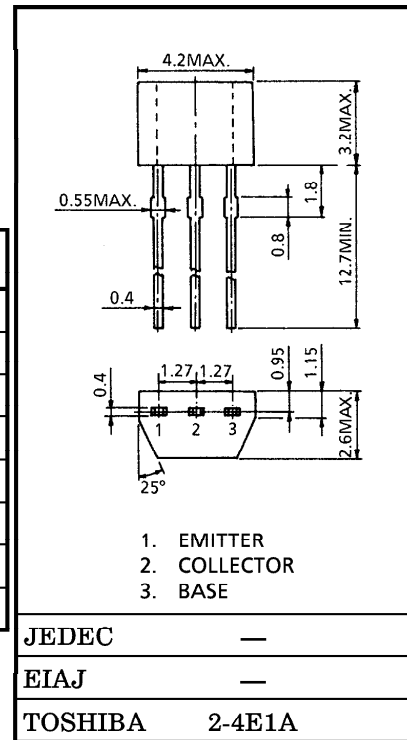
FOR AUDIO AMPLIFIER APPLICATIONS

Unit in mm

- High DC Current Gain : $h_{FE(1)} = 100 \sim 320$
- Complementary to 2SA1150

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	35	V
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C	800	mA
Base Current	I _B	160	mA
Collector Power Dissipation	P _C	300	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Weight : 0.13g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CB0}	V _{CB} = 35V, I _E = 0	—	—	0.1	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 5V, I _C = 0	—	—	0.1	μA
Collector-Emitter Breakdown Voltage	V (BR) CEO	I _C = 10mA, I _B = 0	30	—	—	V
DC Current Gain	h _{FE(1)} (Note)	V _{CE} = 1V, I _C = 100mA	100	—	320	
	h _{FE(2)}	V _{CE} = 1V, I _C = 700mA	35	—	—	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 500mA, I _B = 20mA	—	—	0.5	V
Base-Emitter Voltage	V _{BE}	V _{CE} = 1V, I _C = 10mA	0.5	—	0.8	V
Transition Frequency	f _T	V _{CE} = 5V, I _C = 10mA	—	120	—	MHz
Collector Output Capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f = 1MHz	—	13	—	pF

Note : h_{FE(1)} Classification O : 100~200, Y : 160~320

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